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Rev. 04/03

Docket No. ELM-1 Cont. 13

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/724,282 Confirmation No.: 5846

Filed: December 19, 2003

For : MEMBRANE 3D IC FABRICATION

Group Art Unit : 2814

Examiner : Not yet assigned

New York, New York

July 16, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information Disclosure

Statement in the above-identified application. This

Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Poh

Registration No. 51,176

Agent for Applicants

FISH & NEAVE

Customer No. 1473

1251 Avenue of the Americas

New York, New York 10020-1105

Tel.: (212) 596-9000

I hereby certify that this Correspondence is being deposited with the U.S. Postal Service as First

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P.O. Box 1450

Alexandrian VA 22313-1450 on

Signature of Person Signing

ELM-1 Cont.13



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Examiner : Not yet assigned

Hon. Commissioner for Patents

P.O. Box 1450

Alexandrian, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

U.S. Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81

Kubacki	4,262,631	04/21/8
Shioya et al.	4,394,401	07/19/8
Trenkler et al.	4,401,986	08/30/8
Thomas et al.	4,416,054	11/22/8
Takagi et al.	4,539,068	09/03/8
Reid et al.	4,585,991	04/29/8
Yasumoto et al.	4,612,083	09/16/8
Belanger et al.	4,617,160	10/14/8
Shimizu et al.	4,618,397	10/21/8
Schmitz	4,618,763	10/21/8
Christensen	4,663,559	05/05/8
Burns et al.	4,684,436	08/04/8
Hatada	4,693,770	09/15/8
Maeda et al.	4,702,336	10/27/8
Seibert et al.	4,702,936	10/27/8
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Stevenson	4,721,938	01/26/8
Reid	4,761,681	08/02/8
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Freeman	4,810,673	03/07/8
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Leedy	4,924,589	05/15/9
Borel et al.	4,940,916	07/10/9
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Mauger	4,966,663	10/30/9
Leedy	4,994,735	02/19/9
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Allen et al.	5,010,024	04/23/9
Leedy	5,020,219	06/04/9
Leedy	5,034,685	07/23/9
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Machado et al.	5,098,865	03/24/9
Leedy	5,103,557	04/14/9
Mauger	5,110,373	05/05/9
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	5,111,278	05/26/9
_		03/20/3
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Tuckerman	5,274,270	12/28/93
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Nakanishi et al.	5,284,796	02/08/94
Leedy	5,323,035	06/21/94
Wojnarowski	5,324,687	06/28/94
Leedy	5,354,695	10/11/94
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	5,363,021	11/08/94
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Leedy	5,946,559	08/31/99
Leedy	5,985,693	11/16/99
Cutter et al.	5,998,069	12/07/99
Leedy	6,008,126	12/28/99
Leedy	6,020,257	02/01/00
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"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).

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Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium, "pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be:

(1) fully considered by the Patent and Trademark Office
during the examination of this application; and (2) printed
on any patent which may issue on this application.

Applicant requests that a copy of Form PTO-1449, as
considered and initialized by the Examiner, be returned with
the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

hereby certify that this Correspondence is being deposited with the U.S. Postal Service as First

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Addressed to:

Commissioner for Patents P.O. Box 1450

Claire J. Saintik

Alexandria, VA 22313-1450 on

Aloxandra, VA 2231371400 01

Person Signing

Philip R. Poh

Registration No. 51,176

Agent for Applicant

FISH & NEAVE

Customer No. 1473

1251 Avenue of the Americas New York, New York 10020-1104

Tel.: (212) 596-9000

FORM PTO-1449

P E CO

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM-1 Cont. 13	APPLICATION NO. 10/724,282
APPLICANT Glenn J. Leedy	CONFIRMATION NO. 5846
FILING DATE December 19, 2003	GROUP 2814

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
INITIAL	Re. 34,893	04/04/95	Fujii et al.	257	419	AFFROFRIATE
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
· · · · · · · · · · · · · · · · · · ·	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	-
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
·	4,693,770	09/15/87	Hatada	156	151	-

EXAMINER

FORM PTO-1449			OF COMMERCE DEMARK OFFICE	ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/724,282	
	FORMATION FATEMENT B			APPLICANT Glenn J. Leedy		CONFIRMATION NO 5846	
	TATEMENT D	TAPPLIC	AIV1	FILING DAT December 1		GROUP 2814	
4,702,3	336 1	0/27/87	Maeda et al.	180	197		
4,702,9		0/27/87	Seibert et al.	427	583		
4,706,	166 1	1/10/87	Go	361	403		
4,721,9	938 0	1/26/88	Stevenson	338	4		
4,761,0	681 0	8/02/88	Reid	357	68		
4,784,	721 1	1/15/88	Holmen et al.	156	647		
4,810,6		3/07/89	Freeman	438	386		
4,825,2		4/25/89	Mattox et al.	257	639		
4,857,4		8/15/89	Tam et al.	438	619		
4,924,		5/15/90	Leedy	438	6		
4,940,9		7/10/90	Borel et al.	313	306		
Re B1	4,940,916 1	1/26/96	Borel et al.	315	306		
4,950,9		8/21/90	Vranish et al.	324	207.23		
4,952,4		8/18/90	Lee et al.	428	220		
4,954,		9/04/90	Rokos	257	378		
4,957,		9/18/90	Shinomiya	438	65		
4,965,4		0/23/90	Young et al.	200	83 N		
4,966,0		0/30/90	Mauger	205	656		
4,994,		2/19/91	Leedy	324	158		
5,008,0		4/16/91	Keogh et al.	324	207.17		
5,010,0		4/23/91	Allen et al.	438	659		
5,020,	219 0	6/04/91	Leedy	29	846		
5,034,0		7/23/91	Leedy	324	158 F		
5,070,0		2/03/91	Greenwald et al.	437	3		
5,071,	· ·	2/10/91	Findler et al.	156	647		
5,098,		3/24/92	Machado et al.	438	788		
5,103,		4/14/92	Leedy	29	832		
5,110,		5/05/92	Mauger	148	33.2		
5,111,		5/05/92	Eichelberger	357	75		
5,116,		5/26/92	Chan et al.	438	234		
5,130,		7/14/92	Miller	361	393		
5,132,		7/21/92	Roy	438	477		

FORM PTO-1449		NT OF COMMERCE ADEMARK OFFICE		TY. DOC M-1 Cont	KET NO. . 13	APPLICATION NO. 10/724,282	
	FORMATION DISCL			APPLICANT Glenn J. Leedy		CONFIRMATION NO. 5846	
<u> </u>	STATEMENT BY APPLICAN			ING DAT cember 1		GROUP 2814	
-							
5,151,	775 09/29/92	? Hadwin		 357	80		
5,156,	909 10/20/92	Henager, Jr. et al.	- 1	1 28	334		
5,203,	731 04/20/93		4	145	24		
5,225,		Leedy		324	158		
5,236,				228	193		
5,262,		Bureau et al.	4	1 37	183		
5,270,				137	209		
5,273,		Sanders		137	209		
5,274,	270 12/28/93	Tuckerman	1	257	758		
5,279,		Chebi et al.		127	574		
5,284,	796 02/08/94	Nakanishi et al.	4	137	183		
5,323,0	035 06/21/94	Leedy	1	257	48		
5,324,0	687 06/28/94	Wojnarowski	4	137	225		
5,354,0	695 10/11/94		4	138	411		
5,363,0	021 11/08/94	MacDonald		315	366		
5,385,9	909 01/31/95	Nelson et al.		514	291		
5,385,0	632 01/31/95	Goossen		156	630		
5,420,4	458 05/30/95	Shimoji	- 2	257	622		
5,424,9	920 06/13/95	Miyake		361	735		
5,426,0	072 06/20/95		4	137	208		
5,426,	363 06/20/95	Akagi et al.	:	324	239		
5,432,4	444 07/11/95	Yasohama et al.	:	324	240		
5,432,				365	63		
5,434,				324	67		
5,451,4	i		4	130	313		
5,453,4				137	203		
5,457,8				29	895		
5,476,8				137	132		
5,489,				137	208		
5,502,0	i			365	51		
5,512,	i i		4	130	30		
5,527,0			4	130	5		

FORM PTO-1449	U.S. DEPARTMEN PATENT AND TRA	T OF COMMERCE DEMARK OFFICE	ATTY. DOC ELM-1 Conf		APPLICATION NO. 10/724,282	
	FORMATION DISCLO		APPLICAN Glenn J. Le		CONFIRMATION NO. 5846	
3	TATEMENT DI APPLI	CANT	FILING DAT		GROUP 2814	
5,529,	829 06/25/96	Koskenmaki et al.	428	167		
5,534,	1	Frye et al.	437	209		
5,555,		Toshiaki et al.	365	200		
5,563,		Ramm et al.	437	51		
5,571,		Leedy	437	51	,-	
5,580,		Leedy	430	5		
5,581,	•	Ludwig et al.	365	63		
5,582,		Pierrat	430	5		
5,583,		Hornbeck	359	291		
5,592,	*	Leedy	257	347		
5,592,		Leedy	257	619		
5,595,		Heijboer	439	20		
5,606,		Noda	257	226		
5,627,		Tennant et al.	438	113		
5,629,		Leedy	430	313		
5,633,		Leedy	435	228		
5,637,		Val	438	686		
5,654,		Leedy	430	315	·	
5,654,		Leedy	438	25		
5,656,		Hudak et al.	438	15		
5,675,	1	Chen et al.	257	774		
5,694,		Ohara et al.	395	566		
5,725,		Leedy	430	315		
5,750,		Weise et al.	427	579		
5,760,		Bozso et al.	257	777		
5,773,		Okonogi	428	446		
5,786,		Rolfson	430	5		
5,793,		Zavracky et al.	257	777		
5,831,		Ray	257	48		
5,834,		Leedy	438	107		
5,840,		Leedy	438	6		
5,856,		Ito et al.	257	370		

FORM PTO-1				OF COM		ATTY. DOC ELM-1 Con		APPLICATIO 10/724,282	N NO.
	INFORMATIC STATEMENT					APPLICAN ^T Glenn J. Le		CONFIRMAT 5846	TION NO.
	STATEMENT	IDIAF	PLIC	ANI		FILING DAT		GROUP 2814	_
	5,868,949	02/09/	99	Sotokaw	a et al.	216	18		
	5,869,354	02/09/	99	Leedy		438	110		
	5,870,176	02/09/	99	Sweatt e	t al.	355	53		
	5,880,010	03/09/	99	Davidsor	1	438	455		
	5,882,532	03/16/	99	Field et a	al.	216	2		
	5,902,118	05/11/	99	Hübner		438	106		
	5,915,167	06/22/	99	Leedy		438	108		
	5,946,559	08/31/	99	Leedy		438	157		
	5,985,693	11/16/	99	Leedy		438	107		
	5,998,069	12/07/	99	Cutter et	al.	430	5		
	6,008,126	12/28/	99	Leedy		438	667		
	6,020,257	02/01/	00	Leedy		438	626		
	6,045,625	04/04/	/00 Houston		148		33.3		
	6,084,284	07/04/	00	Adamic,	Jr.	257	506		
	6,097,096	08/01/	00	Gardner	et al.	257	777		
	6,133,640	10/17/	00	Leedy		257	778		
	6,194,245 B1	02/27/	01	Tayanak	а	438	57		
	6,197,456 B1	03/06/	01	Aleshin	et al.	430	5		
	6,208,545 B1	03/27/	01	Leedy		365	51		
	6,236,602 B1	05/22/	01	Patti		365	201		
	6,261,728 B1	07/17/	01	Lin		430	30		
	6,288,561 B1	09/11/				324	760		
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